

2SH16

Silicon N-Channel IGBT

HITACHI

1st. Edition
Nov. 1994

Application

High speed power switching

Features

- High speed switching
- Low on saturation voltage

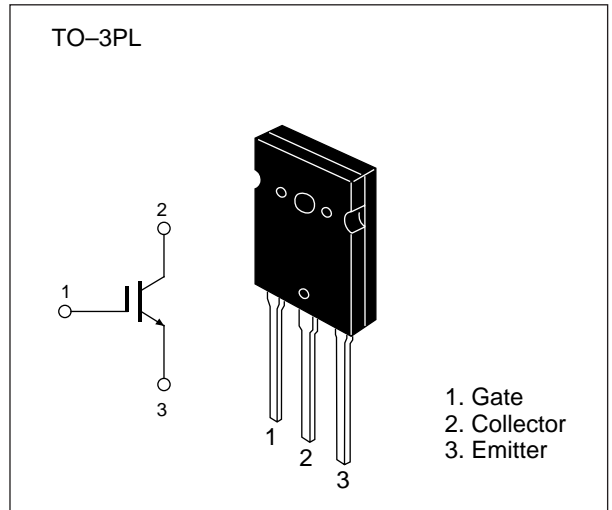


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	600	V
Gate to emitter voltage	V_{GES}	± 20	V
Collector current	I_C	75	A
Collector peak current	$i_{c(\text{peak})}$	150	A
Collector dissipation	P_C^*	200	W
Channel temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

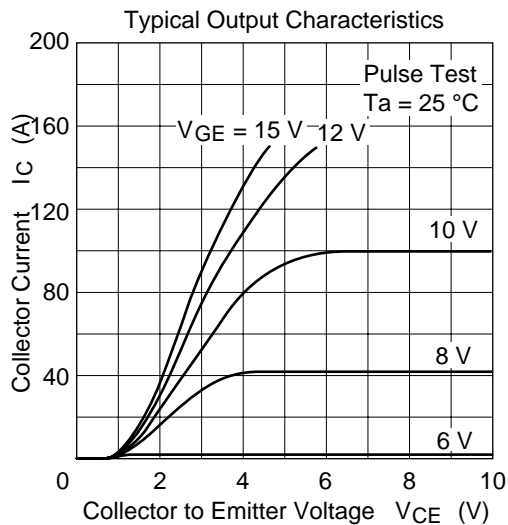
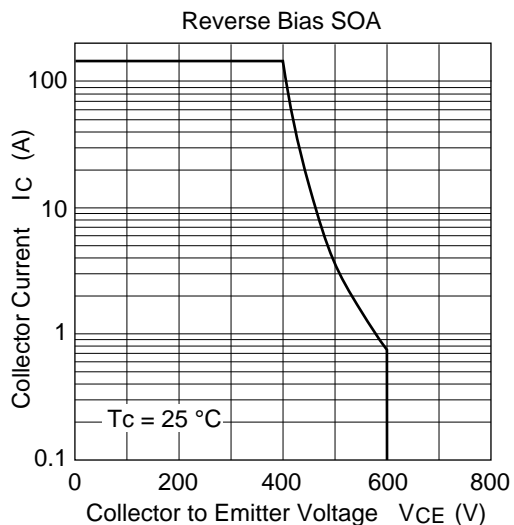
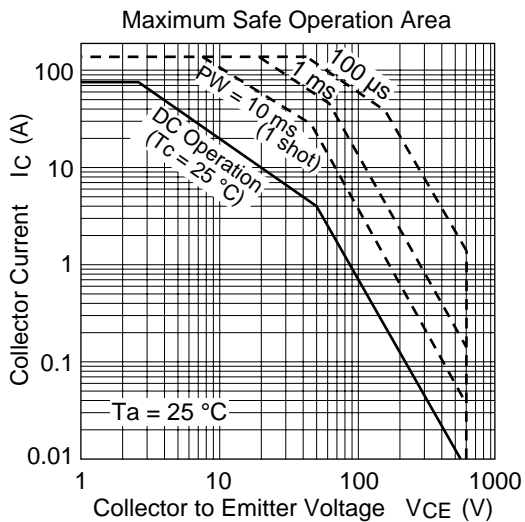
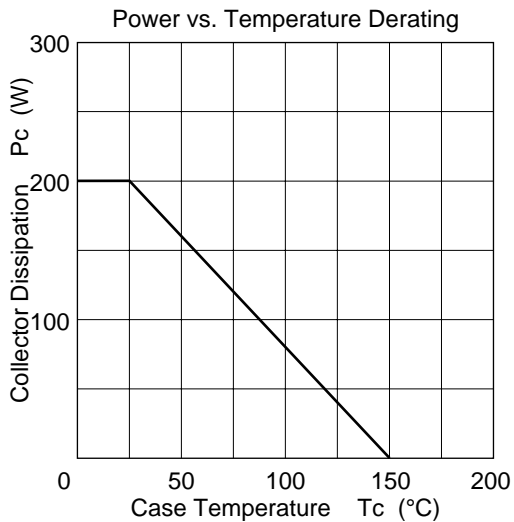
* Value at $T_c = 25^\circ\text{C}$

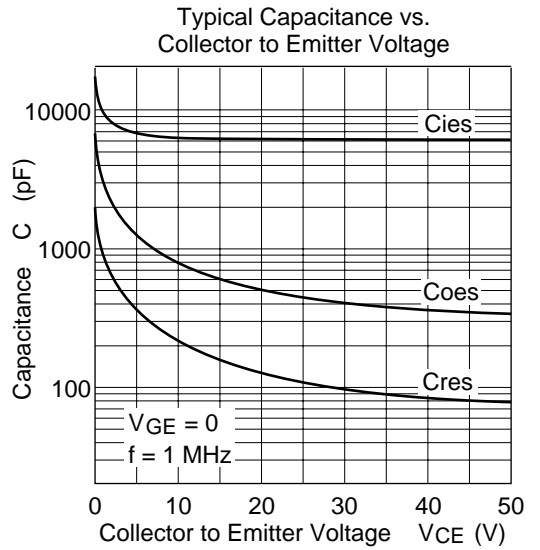
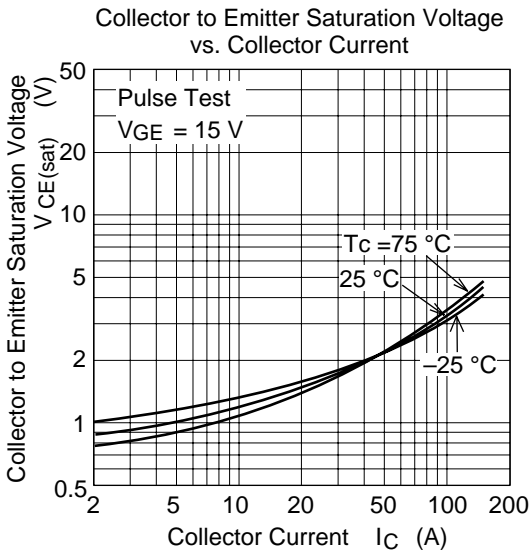
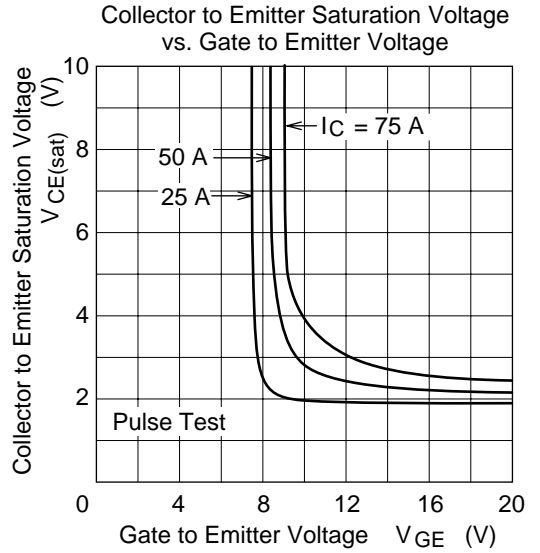
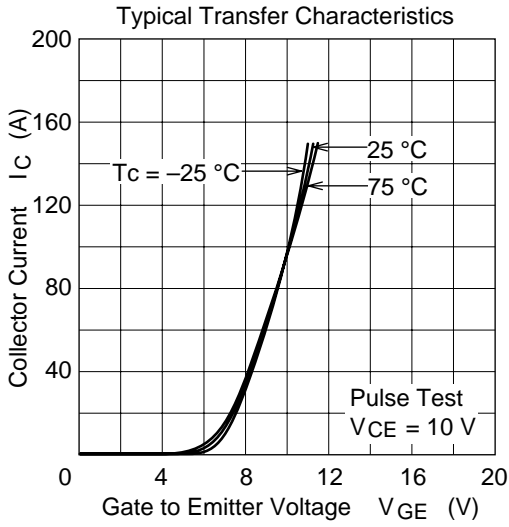
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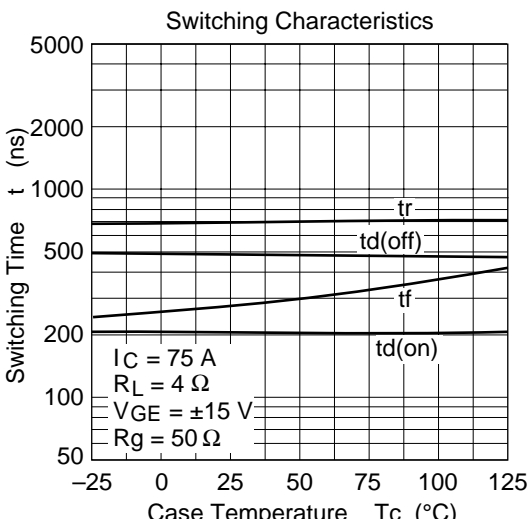
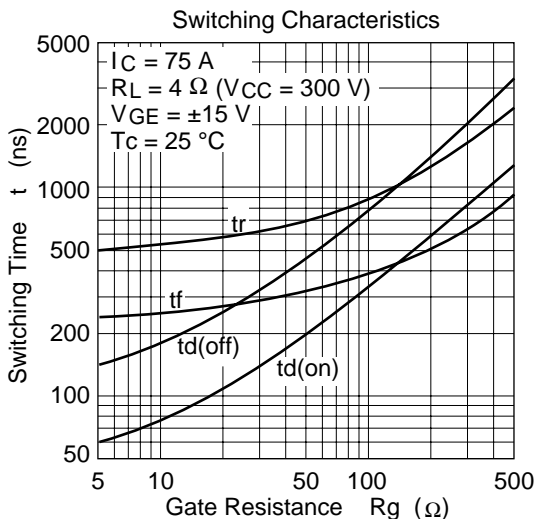
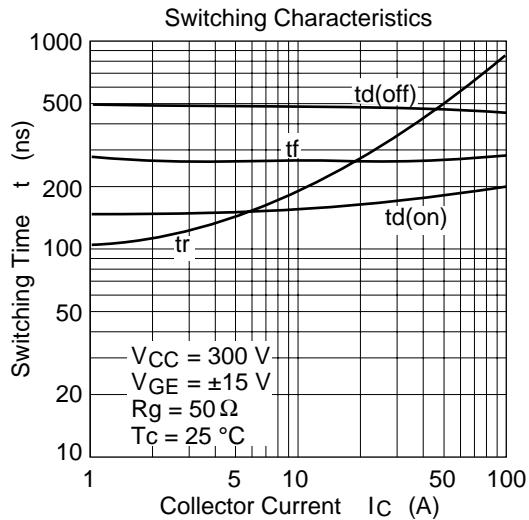
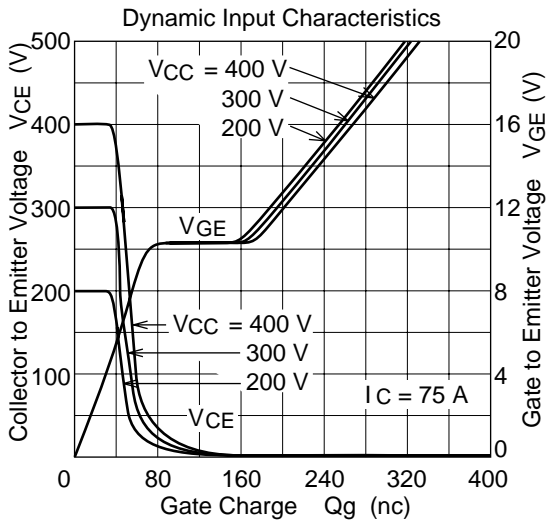
Table 2 Electrical Characteristics ($T_a = 25^\circ\text{C}$)

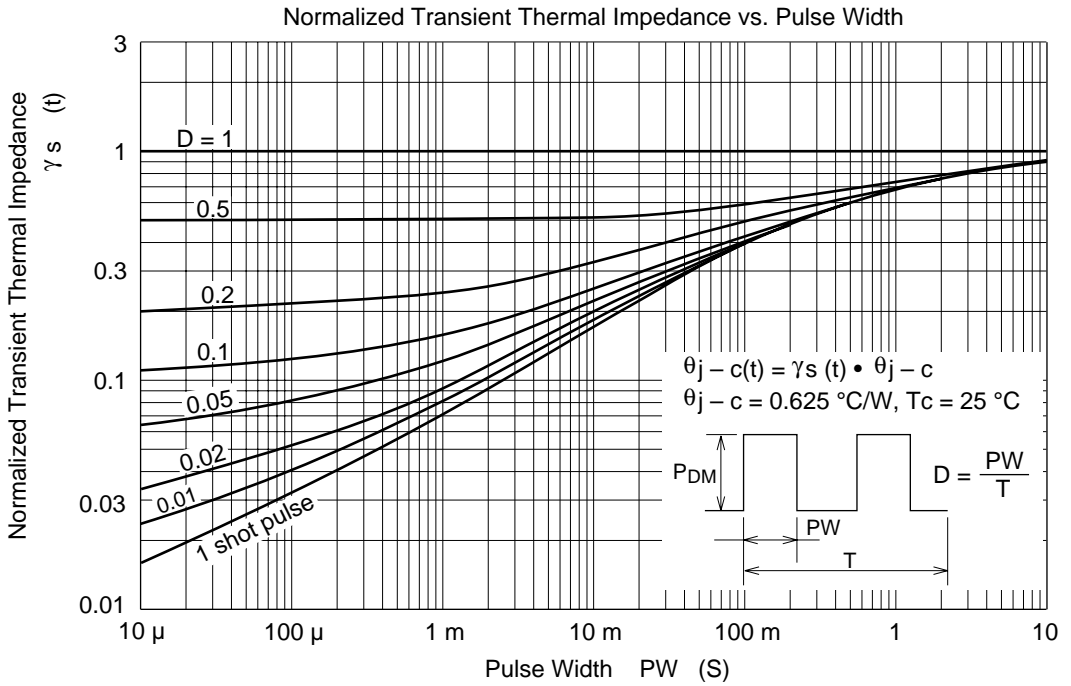
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	600	—	—	V	$I_C = 100 \mu\text{A}, V_{GE} = 0$
Zero gate voltage collector current	I_{CES}	—	—	0.5	mA	$V_{CE} = 600 \text{ V}, V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	± 1	μA	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff current	$V_{GE(off)}$	3.0	—	5.0	V	$I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	2.0	—	V	$I_C = 35 \text{ A}, V_{GE} = 15 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	2.6	3.3**	V	$I_C = 75 \text{ A}, V_{GE} = 15 \text{ V}$
Input capacitance	C_{ies}	—	6200	—	pF	$V_{CE} = 10 \text{ V}, V_{GE} = 0,$ $f = 1 \text{ MHz}$
Switching time	t_r	—	700	—	ns	$I_C = 75 \text{ A},$ $R_L = 4 \Omega,$ $V_{GE} = \pm 15 \text{ V}$ $R_g = 50 \Omega$
	t_{on}	—	900	—		
	t_f	—	300	600		
	t_{off}	—	800	1600		

** $V_{CE(sat)2}$ is specified at the correlated test condition ($I_C=50\text{A}$)

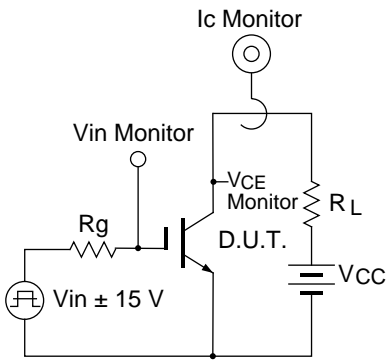




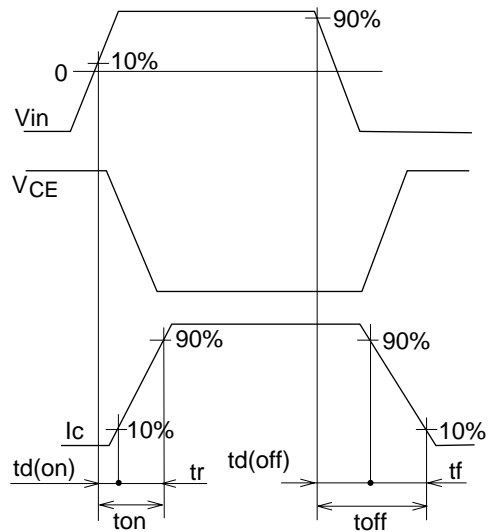




Switching Time Test Circuit



Waveforms



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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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